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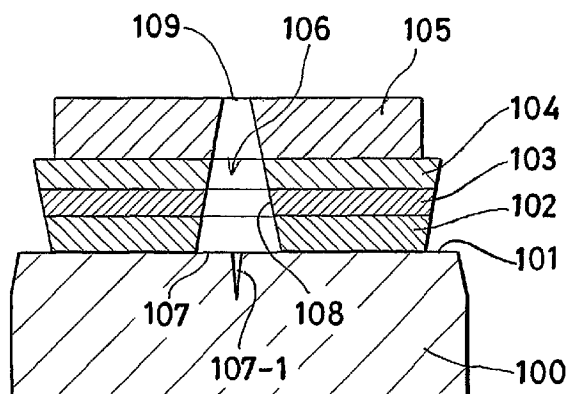
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(54) Title: NITRIDE SEMICONDUCTOR LIGHT-EMITTING DEVICE AND METHOD FOR FABRICATION THEREOF



(57) Abstract: A nitride semiconductor light-emitting device includes a substrate, a nitride semiconductor layer incorporating therein a first electroconductive semiconductor layer, a light-emitting layer and a second electroconductive semiconductor layer, a transparent electrode contiguous to at least part of a first surface of the second electroconductive semiconductor layer, and a second electrode contiguous to the first electroconductive semiconductor layer; wherein the substrate has a first surface thereof provided with a first region exposed by removal of a first part of the nitride semiconductor layer in a peripheral part of the device and a second region exposed by removal of at least a second part of the nitride semiconductor layer contiguous to the transparent electrode except the peripheral part of the device till the substrate. A method for the production of the device includes removing a first part of the nitride semiconductor layer in a peripheral part of the device till the substrate is exposed to form a first exposed region thereof and removing at least a second part of the nitride semiconductor layer contiguous to the transparent electrode except the peripheral part of the device till the substrate is reached to form a second exposed region thereof, wherein the steps are taken by combining the removal with a laser and the removal by wet etching.



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